IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

priority Application Serial No	09/633,556
priority Filing Date	August 7, 2000
Inventor G	iurtej S. Sandhu et al.
Assignee Mi	cron Technology, Inc.
priority Group Art Unit	2813
priority Examiner	Laura M. Schillinger
Attorney's Docket No	MI22-1896
Title: Methods of Forming a Nitrogen Enriched Region (As	Amended)

PRELIMINARY AMENDMENT

To:

Box Patent Application

Assistant Commissioner for Patents

Washington, D.C. 20231

From:

David G. Latwesen, Ph.D. (Tel. 509-624-4276; Fax 509-838-3424)

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In the Specification

Replace the title with --Methods of Forming a Nitrogen Enriched Region--.

At page 1, before the "Technical Field" section, please insert:

-- CROSS REFERENCE TO RELATED APPLICATION

This patent resulted from a divisional application of U.S. Patent Application Serial No. 09/633,556, which was filed on August 7, 2000.--.

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In the Claims

Claims 1-10 and 20-47 are canceled.

REMARKS

Claims 1-10 and 20-47 are canceled, leaving claims 11-19 pending in the application. Applicant requests substantive examination of pending claims 11-19.

Respectfully submitted,

Dated:

David G. Latwesen, Ph.D.

Reg. No. 38,533

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Inventor Gurtej S. Sandhu et al.
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VERSION WITH MARKINGS TO SHOW CHANGES MADE ACCOMPANYING PRELIMINARY AMENDMENT

In the Specification

The replacement specification paragraphs incorporate the following amendments. Underlines indicate insertions and strikeouts indicate deletions.

The title is amended as follows: Transistor Structures, Methods of Incorporating Nitrogen into Silicon-Oxide-Containing Layers; and Methods of Forming Transistors <u>Methods of Forming a Nitrogen Enriched Region</u>

The following is inserted on p. 1 before the "Technical Field" section,

CROSS REFERENCE TO RELATED APPLICATION

This patent resulted from a divisional application of U.S. Patent Application

Serial No. 09/633,556, which was filed on August 7, 2000.

In the Claims

Claims 1-10 and 20-47 are canceled.

-END OF DOCUMENT-